

Low lattice thermal conductivity and high thermoelectric figure of merit in Na₂MgSnCong Wang,¹ Y. B. Chen,² Shu-Hua Yao,¹ and Jian Zhou^{1,3,*}¹*National Laboratory of Solid State Microstructures and Department of Materials Science and Engineering, Nanjing University, Nanjing 210093, China*²*National Laboratory of Solid State Microstructures and Department of Physics, Nanjing University, Nanjing 210093, China*³*Collaborative Innovation Center of Advanced Microstructures, Nanjing University, Nanjing 210093, China*

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Thermoelectric materials enable the harvest of waste heat and direct conversion into electricity. In search of high efficient thermoelectric materials, low thermal conductivity of a material is essential and critical. Here, we have theoretically investigated the lattice thermal conductivity and thermoelectric properties of layered intermetallic Na₂MgSn and Na₂MgPb based on the density functional theory and linearized Boltzmann equation with the single-mode relaxation-time approximation. It is found that both materials exhibit very low and anisotropic intrinsic lattice thermal conductivity. Despite the very low mass density and simple crystal structure of Na₂MgSn, its lattice thermal conductivities along *a* and *c* axes are only 1.77 and 0.81 W/m K respectively at room temperatures. When Sn is replaced by the heavier element Pb, its lattice thermal conductivities decrease remarkably to 0.56 and 0.31 W/m K respectively along *a* and *c* axes at room temperature. We show that the low lattice thermal conductivities of both materials are mainly due to their short phonon lifetimes and phonon mean free path. Combined with previous experimental measurements, the metallic Na₂MgPb cannot be a good thermoelectric material. However, we predict that the semiconducting Na₂MgSn is a potential room-temperature thermoelectric material with a considerable *ZT* of 0.36 at 300 K. Our calculations not only imply that the intermetallic Na₂MgSn is a potential thermoelectric material, but also can motivate more theoretical and experimental works on the thermoelectric researches in simple layered intermetallic compounds.

DOI: [10.1103/PhysRevB.99.024310](https://doi.org/10.1103/PhysRevB.99.024310)**I. INTRODUCTION**

Thermoelectrical (TE) materials, which can directly convert heat to electricity, have been extensively studied for the last several decades since they play an important role in the area of environmentally friendly energy technology [1,2]. The conversion efficiency of TE materials is usually evaluated by a dimensionless figure of merit, $ZT = S^2\sigma T/\kappa$, where *S*, σ , *T*, and κ are the Seebeck coefficient, electrical conductivity, absolute temperature, and thermal conductivity respectively. The thermal conductivity κ of a material can be further divided into two items: $\kappa = \kappa_e + \kappa_L$, where κ_e and κ_L are electronic and lattice thermal conductivity respectively. For practical applications, the *ZT* of a TE material should be at least larger than 1. A *ZT* of 1 can have only 10% of Carnot efficiency. But a higher *ZT* of 4 can realize 30% of Carnot efficiency and thus be comparable with many modern engines, such as home refrigeration [3]. However, these physical quantities (*S*, σ , and κ) in the same material are difficult to be tuned separately due to their internal relationship. In general, the electrical conductivity (σ) and electronic thermal conductivity (κ_e) will increase with the increase of carrier concentration, while the Seebeck coefficient (*S*) will decrease with it [1]. Therefore, most good TE materials are semiconductors, such as IV-VI compounds PbTe [4] and SnSe [5,6].

On the other hand, the lattice thermal conductivity (κ_L) is not directly related to the carrier concentration. Tuning the

lattice thermal conductivities is an effective method to tune the *ZT* values of materials. Typical materials with low lattice thermal conductivities are glasses. However, glasses are bad TE materials because of their very low carrier concentration and mobility compared with crystalline semiconductors [1]. Therefore, good TE materials require a rather peculiar property in the same system: “phonon-glass electron crystal” [7]. In other words, low lattice thermal conductivity is a necessary condition for good TE materials, although not a sufficient one.

In the classic physics picture, the lattice thermal conductivity can be approximated by the formula $\kappa_L = \frac{1}{3}C_v v l = \frac{1}{3}C_v v^2 \tau$, where *C_v*, *v*, *l*, and τ are the heat capacity, phonon velocity, mean free path (MFP), and relaxation time. Furthermore, the phonon velocity is often simply replaced by the sound velocity, which is proportional to $\sqrt{B/\rho}$, where *B* and ρ are the elastic modulus and mass density of a material [8]. Accordingly, one method to design low lattice thermal conductivity materials is to search for high density materials due to their low sound velocities, such as Bi₂Te₃. Besides, complex crystal structural materials usually have low sound velocities, such as Yb₁₄MnSb₁₁ [9]. The other way is to reduce the relaxation time by introduction of defects or nanostructures to scatter phonons [8]. Of course, the intrinsic large anharmonic effect (large Grüneisen parameters) in a material will also reduce the relaxation time by phonon-phonon scattering. A distinct example is SnSe, in which the large anharmonicity leads to its exceptional low lattice thermal conductivity [5]. However, it is not intuitive without quantitative calculations.

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In this work, we predict by first-principles calculations that the layered intermetallic Na_2MgSn and Na_2MgPb have very low and anisotropic intrinsic lattice thermal conductivities. Both materials have a very simple layered structure (eight atoms in the unit cell) and a low mass density (2.82 and 4.01 g/cm^3 for Na_2MgSn and Na_2MgPb , respectively). In particular, we propose that Na_2MgSn is a promising room-temperature TE material. An intermetallic is a solid-state compound exhibiting metallic bonding, defined stoichiometry, and ordered crystal structure. It is a large material family, which has a wide various crystal structure, ranging from 0 to 3 in dimensionality. Despite of their metallic bonding, some intermetallics are semiconductors, which is the precondition for their TE applications. There are many works about the potential TE intermetallic materials such as Mg_3Sb_2 [10–12], CaMgSi [13], $M\text{Ga}_3$ ($M = \text{Fe, Ru, and Os}$) [14], YbAl_3 [15], Zn_4Sb_3 [16], $\text{Al}_2\text{Fe}_3\text{Si}_3$ [17], $M\text{In}_3$ ($M = \text{Ru and Ir}$) [18], $M_2\text{Ru}$ ($M = \text{Al and Ga}$) [19]. In particular, many half- and full-Heusler compounds, which are magnetic intermetallics, are found to be good TE materials [20–23].

In 2012, Yamada *et al.* reported the synthesis, crystal structure, and basic physical properties of hexagonal intermetallic Na_2MgSn [24]. They found that polycrystalline Na_2MgSn is a small band-gap semiconductor with a large Seebeck coefficient of $+390 \mu\text{V/K}$ and an electrical resistivity of about $10 \text{ m}\Omega \text{ cm}$ at 300 K. As a result, the power factor of Na_2MgSn is almost 40% of that of Bi_2Te_3 [24]. Two years later, the same group synthesized the similar intermetallic Na_2MgPb [25], which is a metal with three different phases from 300 to 700 K. In the experiment, the electrical resistivity of Na_2MgPb is much lower than that of Na_2MgSn , which is only $0.4 \text{ m}\Omega \text{ cm}$ at 300 K. From the preliminary experimental results, Na_2MgSn could be a potential TE material. However, the thermal conductivity of Na_2MgSn is not studied yet in both experiments [24,25] and the following theoretical work [26].

The rest of the paper is organized as follows. In Sec. II, we will give the computational details about phonon and thermal conductivity calculations. In Sec. III, we will present the main results about phonon dispersions, temperature, frequency dependent, and accumulated lattice thermal conductivity, group velocity, phonon lifetime, and Seebeck coefficient of Na_2MgSn and Na_2MgPb . Some comparisons between different TE materials are also given. Finally, a short conclusion is presented.

II. COMPUTATIONAL DETAILS

The structure of Na_2MgSn and Na_2MgPb are calculated by the Vienna ab initio simulation package (VASP) [27,28] based on the density functional theory. The projected augmented wave method [29,30] and the generalized gradient approximation with the Perdew-Burke-Ernzerhof exchange-correlation functional [31] are used. The plane-wave cutoff energy is set to be 350 eV. Both the internal atomic positions and the lattice constants are allowed to relax until the maximal residual Hellmann-Feynman forces on atoms are smaller than 0.001 eV/\AA . An $8 \times 8 \times 4 k$ mesh was used in the optimization. We have tested that the van der Waals correction is not

important in the two materials and thus not included in our calculations.

Both the second- and third-order interatomic force constants (IFCs) are calculated by the finite displacement method. The second-order IFCs in the harmonic approximation and the phonon dispersions of Na_2MgSn and Na_2MgPb are calculated by the PHONOPY code [32]. The third-order (anharmonic) IFCs and the lattice thermal conductivity are calculated by the PHONO3PY code [33]. We use a $2 \times 2 \times 2$ supercell (64 atoms) for the calculations of the second- and third-order IFCS in Na_2MgSn and Na_2MgPb . And a q mesh of $20 \times 20 \times 10$ is used for the calculation of lattice thermal conductivity by PHONO3PY code.

We do not use the crude force constants approximation in the third-order IFCs, although we have checked that a cutoff distance of 4 \AA can already obtain a good thermal conductivity. We also checked a larger supercell of $3 \times 3 \times 2$ in Na_2MgSn with a cutoff distance of 5 \AA , and we found that the thermal conductivity changed little.

The Seebeck coefficients of Na_2MgSn and Na_2MgPb are calculated by the BOLTZTRAP2 program [34] with the Boltzmann transport theory. The electron eigenvalues in the whole Brillouin zone are calculated by the VASP code with the hybrid functional of Heyd-Scuseria-Ernzerhof (HSE06) [35] and spin-orbit coupling (SOC). A k mesh of $20 \times 20 \times 10$ is used in the calculations of Seebeck coefficient.

III. RESULTS AND DISCUSSIONS

A. Crystal structure and phonon dispersions

As shown in Fig. 1(a), Na_2MgSn and Na_2MgPb share the same hexagonal crystal structure with the space group of $P6_3/mmc$ (no. 194). It is noted that Na_2MgPb has three phases from 300 to 700 K [25]. However, from 300 to 500 K, Na_2MgPb and Na_2MgSn have the same hexagonal crystal structure [24,25]. Mg and Sn (or Pb) atoms lie in the same plane and form a two-dimensional (2D) honeycomb structure stacking along the c axis. Two layers of Na atoms are intercalated between the adjacent Mg-Sn (or Mg-Pb) layers. This is a little different from other alkali-metal intercalated layered materials, such as Na_xCoO_2 [36] or Na_xRhO_2 [37], in which only one Na layer is intercalated between the adjacent CoO_2 or RhO_2 layers. The Brillouin zone and high-symmetry k points of Na_2MgSn and Na_2MgPb are given in Fig. 1(b).

The optimized lattice constants as well as the experimental ones of Na_2MgSn and Na_2MgPb are given in Table I. We

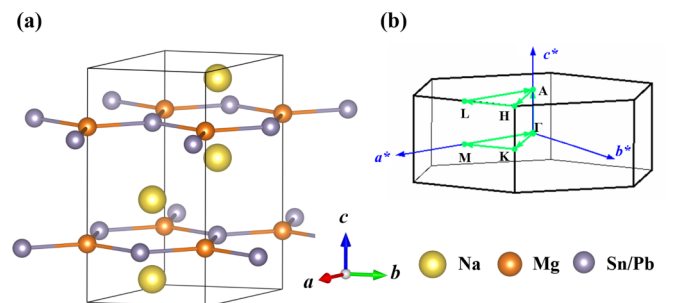


FIG. 1. (a) Layered crystal structure and (b) Brillouin zone and high-symmetry k points of hexagonal Na_2MgSn and Na_2MgPb .

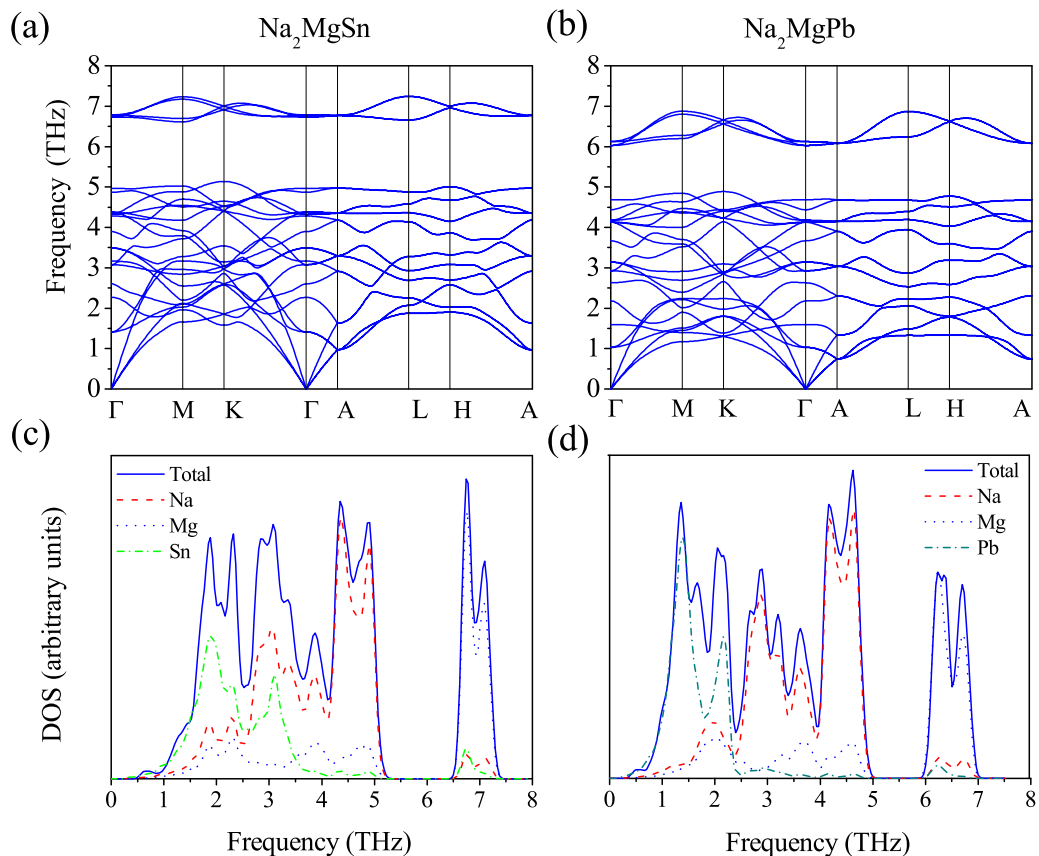


FIG. 2. Calculated phonon dispersions and density of states of hexagonal Na_2MgSn (left column) and Na_2MgPb (right column).

find that the theoretical and experimental lattice constants are very consistent with each other, with the largest difference less than 1%. Our calculated lattice constant is also consistent with Wang's calculation by the generalized gradient approximation with the ultrasoft pseudopotentials (GGA-USP). [26]

Based on the optimized structures, the phonon dispersions and density of states (DOS) of Na_2MgSn and Na_2MgPb are calculated by the PHONOPY code, given in Fig. 2. It is obvious that two materials show very similar phonon dispersions due to the same crystal structures. The highest frequency is about 7.5 and 7.0 THz for Na_2MgSn and Na_2MgPb respectively. There is also a clear band gap from 5 to 6.5 THz for Na_2MgSn and from 5 to 6 THz for Na_2MgPb .

From the phonon DOS in Figs. 2(c) and 2(d), it is found that the high-frequency phonon modes above the band gap

are mainly contributed from the vibrations of Mg ions. This feature is the same for Na_2MgSn and Na_2MgPb . The main difference in phonon DOS between the two materials is the vibrations of Sn and Pb ions. Due to the larger atomic mass of Pb ions, the vibrational frequencies of Pb ions are mainly below 2.5 THz in Na_2MgPb , while the phonon modes of Sn ions extend from 0 to 4 THz in Na_2MgSn . The vibrations of Na ions are similar in both materials, which spread from 0 to 5 THz. It is also noted that the midfrequency phonon modes from 2.5 to 5 THz in Na_2MgPb are mainly contributed from the vibrations of Na ions. However, for the phonon modes in the same frequency range in Na_2MgSn , there is also significant contribution from the vibrations of Sn ions. In other words, the vibrations of Na, Mg, and Pb ions in Na_2MgPb are well separated in different frequency regions, while there is a relatively large overlap in Na_2MgSn .

TABLE I. Calculated and experimental lattice constants of hexagonal Na_2MgSn and Na_2MgPb .

Material	Method	a (Å)	c (Å)
Na_2MgSn	present work	5.0825	10.1075
	expt. (293 K) ^a	5.0486	10.0950
	GGA-USP ^b	5.0085	10.1314
Na_2MgPb	present work	5.1415	10.1873
	expt. (293 K) ^c	5.1102	10.1714

^aFrom Ref. [24].

^bFrom Ref. [26].

^cFrom Ref. [25].

B. Lattice thermal conductivity

Based on the harmonic and anharmonic IFCs, we have calculated the lattice thermal conductivity (κ_L) by using the PHONO3PY code. Figure 3(a) shows the temperature-dependent thermal lattice conductivities along a and c axes of Na_2MgSn and Na_2MgPb , while the average ones are also given in Fig. 3(b). It is quite surprising to find that the κ_L of the two intermetallics are very low. As shown in Fig. 3 and Table II, the κ_L of Na_2MgSn is only 1.77 and 0.81 W/m K along a and c axes at 300 K, while it is even much lower for Na_2MgPb , which is 0.56 and 0.31 W/m K along a and c

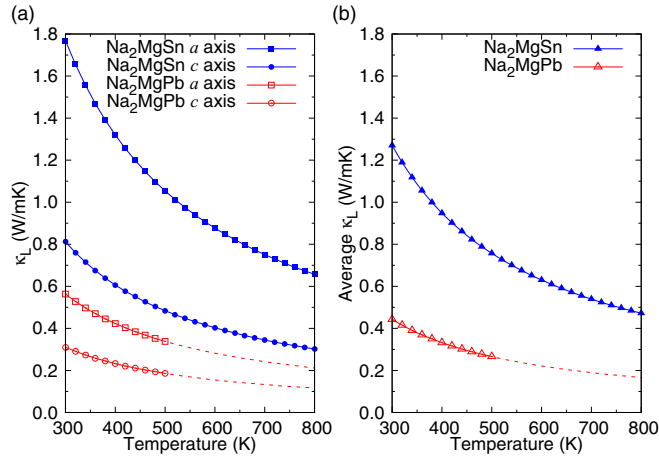


FIG. 3. (a) Calculated lattice thermal conductivities and (b) their average values of hexagonal Na_2MgSn and Na_2MgPb from 300 to 800 K. The red dashed lines mean that the high-temperature lattice thermal conductivities are calculated based on a low-temperature crystal structure of Na_2MgPb .

axes at the same temperature. Specifically, the κ_L along the c axis in Na_2MgPb even approaches the predicted amorphous limit (0.25 W/m K) [38], which is extremely low for crystalline solids. The lattice thermal conductivity of Na_2MgSn is comparable with the typical good TE materials, which will be discussed later. While the lattice thermal conductivity of Na_2MgPb is even smaller than that of the recently found best TE material SnSe, which is 0.8, 2.0, and 1.7 W/m K along a , b , and c axes at 300 K from the first-principles calculations [39]. It is noted that the lattice thermal conductivity of Na_2MgPb above 500 K is meaningless since Na_2MgPb has different crystal structures above that temperature. However, since we mainly focus on the room-temperature behavior of Na_2MgPb , it is not necessary to study its high-temperature thermal conductivity.

Furthermore, Na_2MgSn and Na_2MgPb both show an anisotropic lattice thermal conductivities due to their layered crystal structures. However, the ratio of thermal conductivities between the a and c directions in both materials is smaller than 2. The small anisotropy suggests that easily formed texture structures in layered compounds has not much effect on thermoelectric performance of these compounds.

We also calculated the average lattice thermal conductivity $\bar{\kappa}$, defined by the formula $3/\bar{\kappa} = 2/\kappa_a + 1/\kappa_c$, shown in Fig. 3(b) and Table II. The average $\bar{\kappa}$ for Na_2MgSn and Na_2MgPb are 1.27 and 0.44 W/m K at 300 K respectively.

The electronic thermal conductivity (κ_e) can be estimated by the Wiedemann-Franz law: $\kappa_e = LT\sigma$, where L is the

TABLE II. Calculated lattice thermal conductivities κ_a and κ_c along a and c axes and their average value $\bar{\kappa}$ of hexagonal Na_2MgSn and Na_2MgPb at 300 K. The unit is W/m K.

Material	κ_a	κ_c	$\bar{\kappa}$
Na_2MgSn	1.77	0.81	1.27
Na_2MgPb	0.56	0.31	0.44

TABLE III. Calculated sound velocities along a and c axes of Na_2MgSn and Na_2MgPb . The unit is km/s.

Material	v_a	v_c
Na_2MgSn	2.75	2.41
Na_2MgPb	2.16	1.90

Lorenz number ($2.44 \times 10^{-8} \text{ W } \Omega \text{ K}^{-2}$), σ is the electrical conductivity, and T is the absolute temperature. Since the Wiedemann-Franz law is only applied to metals or heavily doped semiconductors and Na_2MgSn is a semiconductor, we only use the Wiedemann-Franz law to calculate the electronic thermal conductivity of Na_2MgPb . According to previous experiments [25], we can obtain that the electrical resistivity (ρ) of Na_2MgPb is about 0.4 m Ω cm at 300 K. So the electronic thermal conductivity of Na_2MgPb is estimated to be 1.83 W/m K, which is even much larger than the lattice one. For the semiconducting Na_2MgSn , we just ignore its electronic thermal conductivity due to its semiconducting property.

The sound velocity is also calculated by the slopes of three acoustic-phonon branches near the Γ point (see Table III). For each direction, the sound velocity is averaged on the two transversal acoustic modes (TA1 and TA2) and one longitudinal acoustic mode (LA) by the formula $3/v_x^3 = 1/v_{x,TA1}^3 + 1/v_{x,TA2}^3 + 1/v_{x,LA}^3$, where x means the a and c axes. In Table III, we can see that in a and c axes, the sound velocities of Na_2MgSn are both higher than those of Na_2MgPb . For both materials, the sound velocity along a axis is higher than that along the c axis.

We further plot the directional cumulative lattice thermal conductivity with respect to the phonon MFP in Na_2MgSn and Na_2MgPb at 300 K in Fig. 4. It is found that the κ_L of Na_2MgSn is mainly dominated by the phonons whose MFPs are less than 100 nm. However, for Na_2MgPb , the κ_L is mostly contributed by the phonons whose MFPs are less than 20 nm. This indicates that the phonon MFP in Na_2MgPb is much

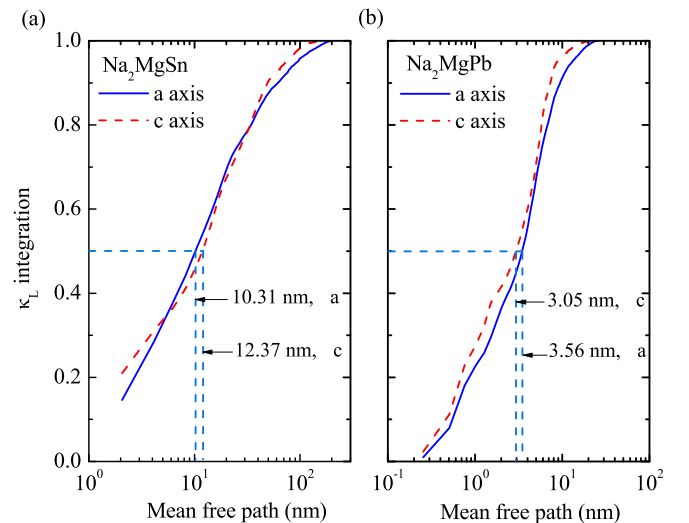


FIG. 4. Normalized directional accumulated lattice thermal conductivities of hexagonal (a) Na_2MgSn and (b) Na_2MgPb at 300 K.

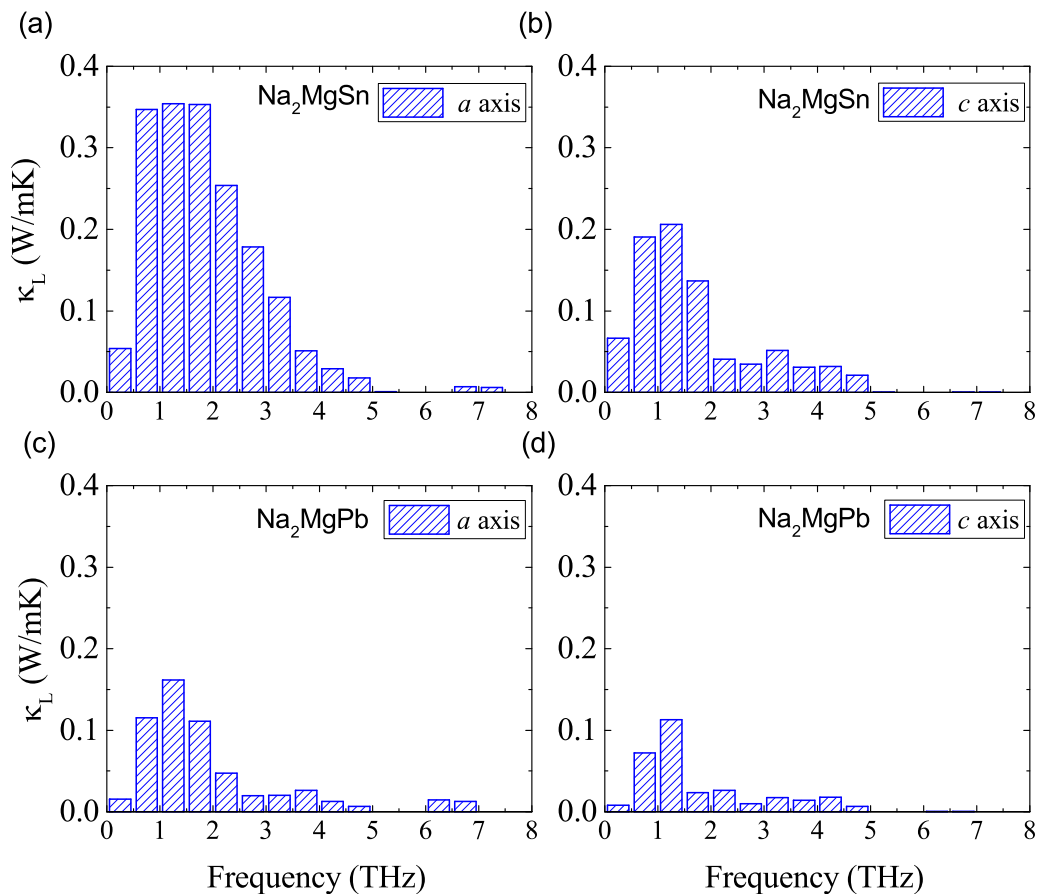


FIG. 5. Frequency-dependent lattice thermal conductivities of Na_2MgSn and Na_2MgPb at 300 K in a and c axes.

shorter than that in Na_2MgSn , leading to a much lower κ_L in Na_2MgPb than that in Na_2MgSn .

We also give the representative MFP (rMFP) for the two materials in Fig. 4. This parameter (rMFP) means that all the phonons whose MFP is shorter than the rMFP will contribute half to the total thermal conductivity. It is clear to see that the rMFP of Na_2MgPb is much shorter than that of Na_2MgSn . For Na_2MgSn , the rMFP along the a and c axes are 10.31 and 12.37 nm respectively, while they are only 3.56 and 3.05 nm along the same axes for Na_2MgPb . The rMFP of Na_2MgPb is even a little shorter than the ones of SnSe, which are 4.1, 4.9, and 5.6 nm along the a , b , and c axes at 300 K from the first-principles calculations [39].

The length of the MFP in Na_2MgSn is shorter than (or comparable with) the size of the crystalline grain of usual crystalline materials, therefore we think that the structural engineering, such as nanostructuring or polycrystalline structures, would be quite challenging in experiment to reduce the thermal conductivity in Na_2MgSn .

C. Frequency-dependent lattice thermal conductivity

Here, we plotted the frequency-dependent lattice thermal conductivity of the two materials, as shown in Fig. 5. In this figure, the width of each column in the histogram is 0.5 THz. The summation of all columns is the total lattice thermal conductivity. In Figs. 5(a) and 5(b), the acoustic and low-frequency optical phonons below 3 THz contribute most

of the thermal conductivity in Na_2MgSn (about 87% along a axis and 83% along c axis). Similarly, in Figs. 5(c) and 5(d), the phonons below 3 THz contribute about 84% of the thermal conductivity along the a axis and 82% along the c axis in Na_2MgPb . On the other hand, the high-frequency optical phonons above the energy gap have negligible contribution to the thermal conductivity.

We also can directly compare the lattice thermal conductivity between Na_2MgSn and Na_2MgPb , since we give the absolute value in Fig. 5. For example, in Figs. 5(a) and 5(c), we can find that the frequency-dependent lattice thermal conductivities of Na_2MgPb along the a axis are much smaller than those of Na_2MgSn in the most of the frequency region (from 0 to 6 THz). Similar behavior can be found in the thermal conductivity along the c axis.

D. Group velocity and phonon lifetime

In order to further understand the low intrinsic thermal lattice conductivity in Na_2MgSn and Na_2MgPb , we also calculated their frequency-dependent phonon group velocities and phonon lifetimes. In Fig. 6, we have given the squares of phonon group velocities of Na_2MgSn and Na_2MgPb , since the lattice thermal conductivity is proportional to the squares of the phonon group velocities. We can see that the squares of the group velocities of Na_2MgPb are smaller than those of Na_2MgSn , which results in the lower thermal conductivity in Na_2MgPb .

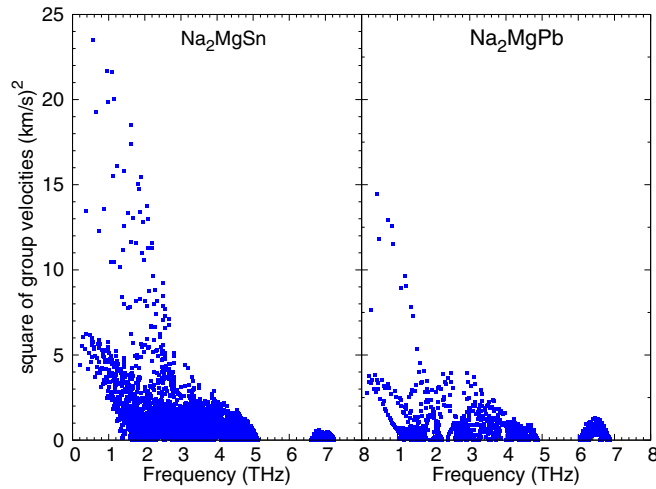


FIG. 6. Calculated square of the group velocities of Na_2MgSn (left) and Na_2MgPb (right).

The frequency-dependent phonon lifetimes of Na_2MgSn and Na_2MgPb are also calculated by the PHONO3PY code from third-order anharmonic IFCs, plotted in Fig. 7. The color bar in Fig. 7 represent the density of phonon modes. In general, we found that the phonon lifetimes of both materials are very short, roughly ranging from 0.4 to 4.5 ps, which are even smaller than those of SnSe (from 0 to 30 ps) [39]. Overall, the lifetimes of the low-frequency phonons below the band gap in Na_2MgSn and Na_2MgPb are similar, both showing a broad distribution with a maximal value about 4.5 ps. But relatively, Na_2MgPb has more phonon modes with shorter lifetimes than those of Na_2MgSn (particularly near 3 THz), which partially accounts for the lower thermal conductivity of Na_2MgPb . On the other hand, the lifetimes of high-frequency phonons above the band gap in the two materials are almost the same; both have a narrow distribution from 0.5 to 1.0 ps.

From the results of frequency-dependent lattice thermal conductivities, group velocities, and phonon lifetimes (from Figs. 5–7), we can conclude that lower group velocities and shorter lifetimes both contribute to the lower thermal conductivity of Na_2MgPb compared with the one of Na_2MgSn .

E. Seebeck coefficient

In order to estimate the ZT , we have also calculated the Seebeck coefficient of two materials, shown in Fig. 8. The electron band structure calculations with HSE06 hybrid functionals and SOC indicate that Na_2MgSn is a small gap (about 0.18 eV) semiconductor, while Na_2MgPb is a semimetal. In Fig. 8(a), the maximal absolute Seebeck coefficient of Na_2MgSn at 300 K is about $250 \mu\text{V}/\text{K}$, which is lower than the experimental value ($390 \mu\text{V}/\text{K}$). The difference of the theoretical and experimental Seebeck coefficient is due to the inaccurate theoretical band gap. In fact, we have also calculated the Seebeck coefficient of Na_2MgSn with hybrid functionals but without SOC and the maximal Seebeck coefficient can reach $480 \mu\text{V}/\text{K}$ at 300 K (with a band gap of 0.34 eV). In Fig. 8(b), it is natural to find that the Seebeck coefficient of metallic Na_2MgPb is quite low. At the Fermi energy, its Seebeck coefficient is about $-22 \mu\text{V}/\text{K}$.

F. Discussion

First, we compare some theoretical physical properties of Na_2MgSn and Na_2MgPb with other well-known TE materials, such as SnSe, SnS, Bi_2Te_3 , and PbTe, shown in Table IV. It is found that Na_2MgSn and Na_2MgPb have comparable lattice thermal conductivities as those TE materials. The main difference is that Na_2MgSn and Na_2MgPb have a much smaller mass density, a smaller bulk modulus, and a relatively higher sound velocity. In particular, the mass density of Na_2MgSn is less than half of the SnSe's, while they almost have the same lattice thermal conductivities. It is a quite unique behavior in low- κ materials. In spite of the very low mass density and

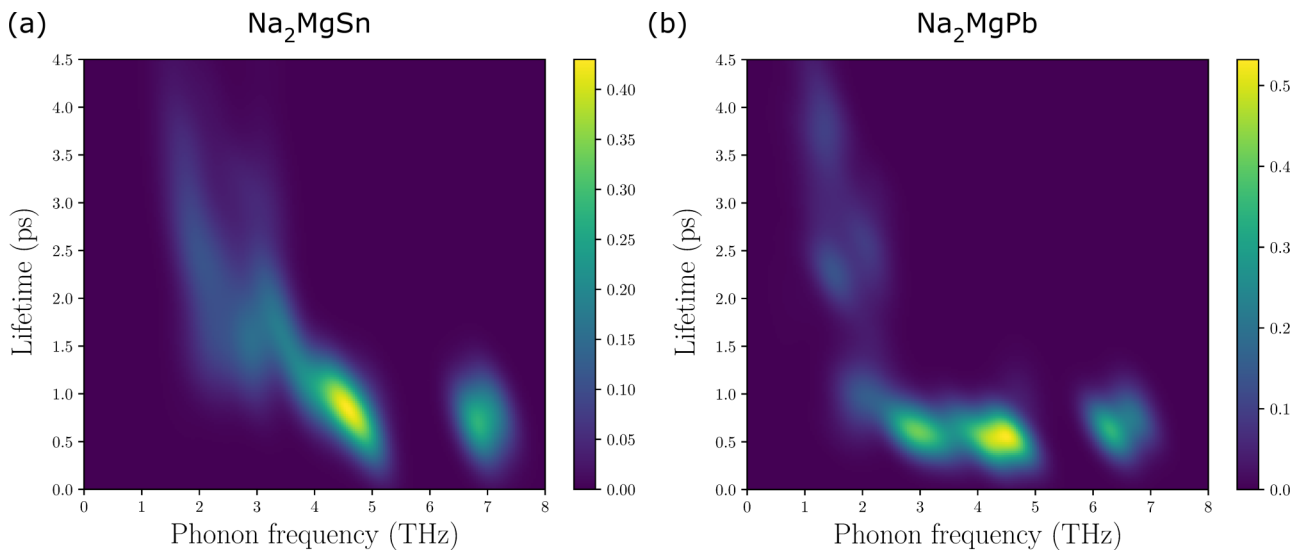


FIG. 7. Calculated phonon lifetimes of (a) Na_2MgSn and (b) Na_2MgPb at 300 K. The color in the figure represents the phonon density. Brighter color means a higher phonon density.

TABLE IV. Comparison of theoretical lattice thermal conductivity (κ_L), mass density (ρ), bulk modulus (B), sound velocity (v), rMFP, and maximal phonon lifetime (τ) of Na_2MgSn and Na_2MgPb at 300 K with other typical TE materials. All physical quantities except the mass density are theoretical ones. The data of Na_2MgSn and Na_2MgPb are from the present work. The (a), (b), and (c) in the table indicates the a , b , and c axes respectively.

Material	κ_L (W/m K)	ρ (g/cm ³)	B (GPa)	v (km/s)	rMFP (nm)	τ (ps)
Na_2MgSn	1.77(a)/0.81(c)	2.82 [24]	30.6	2.75(a)/2.41(c)	10.31(a)/12.37(c)	~ 4.5
Na_2MgPb	0.56(a)/0.31(c)	4.01 [25]	27.0	2.16(a)/1.90(c)	3.56(a)/3.05(c)	~ 4.5
SnSe [39]	0.8(a)/2.0(b)/1.7(c)	~ 6.1 [42]	39.4	0.40(a)/0.63(b)/0.58(c)	5.6(a)/4.9(b)/4.1(c)	~ 30
SnS [39]	0.9(a)/2.3(b)/1.6(c)	5.1 [43]	41.6	0.44(a)/0.71(b)/0.60(c)	4.3(a)/5.2(b)/4.0(c)	~ 30
Bi_2Te_3	1.2(a)/0.4(c) [44]	7.88 [45]	36.4 [45]	1.68(a)/1.79(c) [46]	1.5(a) [44]	
PbTe	2.1 [47]	8.24 [48]	45.51 [49]	1.98 [49]	6 [47]	~ 100 [47]

high sound velocity, Na_2MgSn and Na_2MgPb show a very low lattice thermal conductivity due to their large anharmonicity. From Table IV, we can see that the maximal lifetime of Na_2MgSn and Na_2MgPb is much smaller than those of SnSe, SnS, Bi_2Te_3 , and PbTe. We think the large anharmonicity is probably due to the Na intercalated layered structures. In Na_2MgSn and Na_2MgPb , there are two layers of Na ions loosely confined between adjacent Mg-Sn (or Mg-Pb) layers. The possible rattling modes of the Na ions could suppress the lattice thermal conductivity, as has been found in some cage structure materials, such as $\text{Ba}_8\text{Ga}_{16}\text{Ge}_{30}$ [40] and layered structure materials, such as Na_xCoO_2 [41].

Second, we can compare some experimental properties of Na_2MgSn and Na_2MgPb with other TE materials, as shown in Table V. It is found that Na_2MgSn has a high Seebeck coefficient at room temperatures, which is much higher than those of Bi_2Te_3 and PbTe, but a little lower than those of SnSe and SnS. The calculated thermal conductivity of Na_2MgSn is larger than that of SnSe, but lower than that of Bi_2Te_3 and PbTe. The main drawback of Na_2MgSn is its low electrical conductivity, which is almost one order lower than that of

Bi_2Te_3 . Based on the experimental and calculated data in Table V, we can estimate that the ZT of Na_2MgSn is about 0.36 at 300 K, which is lower than that of Bi_2Te_3 , but much higher than those of PbTe, SnSe, and SnS at the same temperatures. It is noted that the SnSe and SnS have the best performance at high temperatures (more than 700 K), while Na_2MgSn would have the highest ZT near the room temperature due to its small band gap.

On the other hand, although Na_2MgPb has an ultralow lattice thermal conductivity, its total thermal conductivity (about 2.27 W/m K) is not small due to the extra contribution of electrons. Its Seebeck coefficient is also very small (about 22 $\mu\text{V}/\text{K}$) due to its metallicity. Therefore the metallic Na_2MgPb cannot be a good TE material, with an estimated ZT of 0.016 at 300 K.

Finally, we would like to give some possible suggestions on how to improve the ZT of Na_2MgSn . From Table V, the estimated ZT of Na_2MgSn is much lower than that of typical TE material Bi_2Te_3 at 300 K, because its electrical conductivity is ten times lower than that of Bi_2Te_3 . Therefore, it is natural to think that if we can improve the electrical conductivity of Na_2MgSn , then we can possibly improve its ZT . The experimental electrical conductivity is measured based on the polycrystalline sample. If we can grow single crystalline Na_2MgSn , its electrical conductivity could be improved significantly. We note that the thermal conductivity of Na_2MgSn used here is theoretical value, which is of course based on a perfect single crystal. Furthermore, we assume that the Seebeck coefficient will not change significantly from polycrystal to single crystal. If the electrical conductivity of single crystalline Na_2MgSn could increase three times compared with the one of polycrystal, then its ZT could possibly be larger than 1.

On the other hand, Na_2MgPb has a much higher electrical conductivity than those of Na_2MgSn and Bi_2Te_3 , then the Pb doping in Na_2MgSn could improve the electrical conductivity, thus the ZT value.

It is also possible to improve ZT by reducing the thermal conductivity of Na_2MgSn . According to the accumulated lattice thermal conductivities in Fig. 4(a), if we want to reduce 50% of the thermal conductivity of Na_2MgSn , we need to reduce the maximal MFP to about 10 nm by using the structural engineering methods, such as tuning the grain size of polycrystalline sample or making nanostructures. However, this could be quite challenging in experiment due to the very

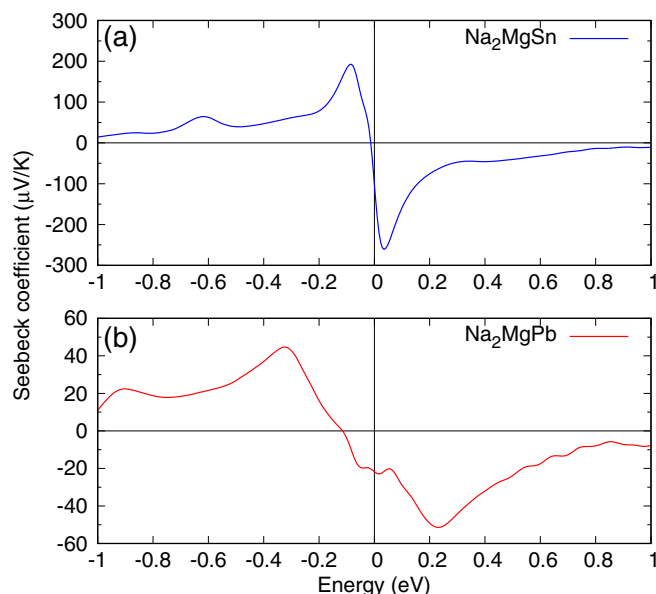


FIG. 8. Calculated Seebeck coefficient of (a) Na_2MgSn and (b) Na_2MgPb at 300 K. The Fermi energy is set to 0.

TABLE V. Comparison of experimental electrical conductivity (σ), absolute Seebeck coefficient (S), total thermal conductivity (κ), and figure of merit ZT of Na_2MgSn and Na_2MgPb at 300 K with other TE materials. The values with * are theoretical ones or estimated ones based on the theoretical results. In the table, only SnSe sample is a single crystal.

Material	σ ($\Omega^{-1} \text{cm}^{-1}$)	S ($\mu\text{V}/\text{K}$)	κ ($\text{W}/\text{m K}$)	ZT
Na_2MgSn [24]	100	390	1.27*	0.36*
Na_2MgPb [25]	2500	22*	2.27*	0.016*
SnSe [5]	1.6(a)/10(b)/10.3(c)	542(a)/522(b)/515(c)	0.46(a)/0.7(b)/0.68(c)	0.03(a)/0.12(b)/0.12(c)
SnS [50]	0.001	400	1.25	3.8×10^{-6}
Bi_2Te_3 [51]	962	226	1.47	1.003
PbTe [48]	200	192	1.7	0.13

short phonon MFP. On the other hand, the atomic doping in Na_2MgSn by Pb or other ions could also reduce the thermal conductivity by introducing more.

IV. CONCLUSIONS

We have studied the lattice thermal conductivities and thermoelectric properties of layered intermetallic Na_2MgSn and Na_2MgPb based on the density functional theory and linearized Boltzmann equation. Despite their very low mass density and simple crystal structure, both materials exhibit very low lattice thermal conductivities, compared with other well-known TE materials. The lattice thermal conductivities along a and c axes of Na_2MgSn are 1.77 and 0.81 W/m K respectively at 300 K, and they are much lower in Na_2MgPb , which are 0.56 and 0.31 W/m K along a and c axes at the same temperature. The main reason of their low thermal conductivity is due to their short phonon lifetimes and phonon mean free path.

Na_2MgPb cannot be a good TE material due to its metallicity. However, we predict that Na_2MgSn is a potential room-temperature TE material with a considerably large ZT of 0.36.

We also suggest that the ZT of Na_2MgSn could be further improved by a different method, such as growing single crystalline Na_2MgSn , doping Pb or other ions in Na_2MgSn , tuning the grain size of polycrystalline sample, or making nanostructures in Na_2MgSn .

Since the intermetallic is a large material family, our work can possibly stimulate further experimental and theoretical works about the thermoelectric research in simple layered intermetallic compounds.

Note Added. Recently, B. Peng *et al.* predicted that Na_2MgPb is a Dirac semimetal, while Na_2MgSn is a trivial indirect semiconductor with a small band gap of about 0.13 eV (with SOC) or 0.29 eV (without SOC) [52].

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